



ELECTRONICS, INC.  
 44 FARRAND STREET  
 BLOOMFIELD, NJ 07003  
 (973) 748-5089  
<http://www.nteinc.com>

## NTE225 Silicon NPN Transistor Linear Amplifier and High Speed Switch

### **Description:**

The NTE225 is a silicon NPN transistor in a TO39 type package (with flange) designed for industrial and commercial equipment. Typical applications include high voltage differential and operational amplifiers, high voltage inverters, and high voltage, low current switching and series regulators.

### **Features:**

- High Voltage Rating:  $V_{CEO(sus)} = 350V$  Max.
- Low Saturation Voltage

### **Absolute Maximum Ratings:**

Collector–Base Voltage, $V_{CBO}$ .....	450V
Collector–Emitter Sustaining Voltage, $V_{CEO(sus)}$ .....	350V
Emitter–Base Voltage, $V_{EBO}$ .....	7V
Collector Current, $I_C$ .....	1A
Base Current, $I_B$ .....	500mA
Total Power Dissipation ( $T_C = +25^\circ C$ ), $P_D$ .....	10W
Operating Junction Temperature Range, $T_J$ .....	$-65^\circ$ to $+200^\circ C$
Storage Temperature Range, $T_{stg}$ .....	$-65^\circ$ to $+200^\circ C$
Thermal Resistance, Junction–to–Case, $R_{thJC}$ .....	$17.5^\circ C/W$
Lead Temperature (During Soldering, 1/32" from seating plane for 10sec Max, $T_L$ .....	$+255^\circ C$

### **Electrical Characteristics:** ( $T_C = +25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Emitter Sustaining Voltage	$V_{CEO(sus)}$	$I_C = 50mA, I_B = 0$ , Base Open, Note 1	350	–	–	V
Collector Cutoff Current	$I_{CEO}$	$V_{CE} = 300V, I_B = 0$	–	–	20	$\mu A$
	$I_{CEV}$	$V_{CE} = 450V, V_{BE} = -1.5V$	–	–	500	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{BE} = 6V, I_C = 0$	–	–	20	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE} = 10V, I_C = 20mA$	40	–	160	
		$V_{CE} = 10V, I_C = 2mA$	30	–	–	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 50mA, I_B = 4mA$	–	–	0.5	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 50mA, I_B = 4mA$	–	–	1.3	V
Small–Signal Current Gain	$h_{fe}$	$V_{CE} = 10V, I_C = 10mA, f = 5MHz$	3	–	–	
Output Capacitance	$C_{ob}$	$V_{CB} = 10V, I_E = 0, f = 1MHz$	–	–	10	pF
Second Breakdown Collector Current	$I_{S/b}$	$V_{CE} = 200V$ , with Base Forward Biased	50	–	–	mA

Note 1. The sustaining voltage ( $V_{CEO(sus)}$ ) **MUST NOT** be measured on a curve tracer.

